



ZTX1049A

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	80	V
Collector-Emitter Voltage	V _{CEO}	25	V
Emitter-Base Voltage	V_{EBO}	5	V
Continuous Collector Current	Ic	4	Α
Peak Pulse Current	I _{CM}	20	Α
Base Current	I _B	500	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	PD	1.5	W
Power Dissipation (Note 6)	P _D	1	W
Thermal Resistance Junction to Ambient (Note 5)	$R_{ heta JA}$	116	°C/W
Thermal Resistance Junction to Ambient (Note 6)	$R_{ heta JA}$	175	°C/W
Thermal Resistance Junction to Lead (Note 7)	$R_{ heta JL}$	63.75	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +200	°C

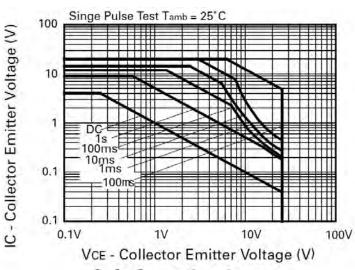
ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	≥ 4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	≥ 400	V	С

Notes:

- 5. For a through-hole device mounted at the seating plane (2.5mm lead length) with the collector lead on 25mm X 25mm 1oz weight copper that is on a single-sided FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
- 6. Same as note (5), except the device is mounted on minimum recommended pad layout with 12mm lead length from the bottom of package to the board.
- 7. Thermal resistance from junction to solder-point at the seating plane (2.5mm from the bottom of package along the collector lead).
- 8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

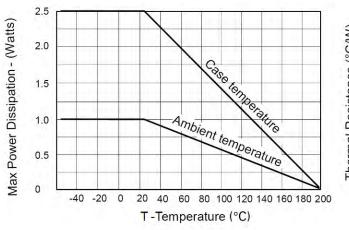
Thermal Characteristics and Derating Information

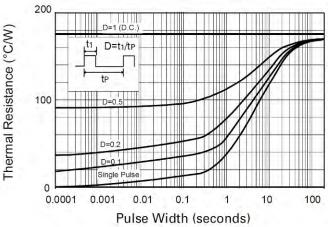






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Derating curve

Maximum transient thermal impedance

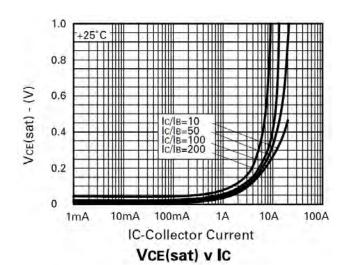
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

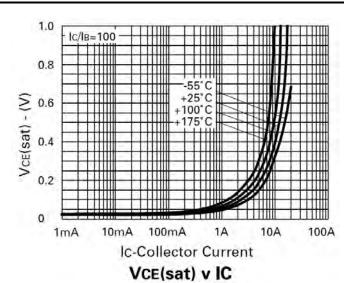
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	80	120	_	V	$I_{C} = 100 \mu A$
Collector-Emitter Breakdown Voltage	BV _{CES}	80	120	_	V	$I_{C} = 100 \mu A$
Collector-Emitter Breakdown Voltage (Note 9)	BV _{CEO}	25	30	_	V	I _C = 10mA
Collector-Emitter Breakdown Voltage	BV _{CEV}	80	120	_	V	$I_C = 100 \mu A, V_{EB} = 1 V$
Emitter-Base Breakdown Voltage	BV _{EBO}	5	8.75	_	V	$I_{E} = 100 \mu A$
Collector Cut-off Current	I _{CBO}	_	0.3	10	nA	V _{CB} = 50V
Collector Emitter Cut-off Current	I _{CES}	_	0.3	10	nA	V _{CES} = 50V
Emitter Cut-off Current	I _{EBO}	_	0.3	10	nA	$V_{EB} = 4V$
Collector-Emitter Saturation Voltage (Note 9)	V _{CE(sat)}	_	30 60 125 155	45 80 180 220	mV	$I_C = 500$ mA, $I_B = 10$ mA $I_C = 1$ A, $I_B = 10$ mA $I_C = 2$ A, $I_B = 10$ mA $I_C = 4$ A, $I_B = 50$ mA
Base-Emitter Saturation Voltage (Note 9)	V _{BE(sat)}	_	890	950	mV	I _C =4A, I _B = 50mA
Base-Emitter Turn-On Voltage (Note 9)	V _{BE(on)}	_	820	900	mV	I _C = 4A, V _{CE} = 2V
DC Current Gain (Note 9)	h _{FE}	250 300 300 200 35	430 450 450 350 70	_ _ 1200 _ _	_	$\begin{split} I_{C} &= 10 \text{mA}, \ V_{CE} = 2 \text{V} \\ I_{C} &= 0.5 \text{A}, \ V_{CE} = 2 \text{V} \\ I_{C} &= 1 \text{A}, \ V_{CE} = 2 \text{V} \\ I_{C} &= 4 \text{A}, \ V_{CE} = 2 \text{V} \\ I_{C} &= 20 \text{A}, \ V_{CE} = 2 \text{V} \end{split}$
Current Gain-Bandwidth Product (Note 9)	f _T	_	180	_	MHz	$V_{CE} = 10V, I_{C} = 50mA$ f = 50MHz
Output Capacitance (Note 9)	C _{obo}	_	45	60	pF	V _{CB} = 10V. f = 1MHz
Turn-On Times	t _{on}	_	125	_	ns	$I_C = 4A$, $I_B = 40mA$, $V_{CC} = 10V$
Turn-Off Times	t _{off}	_	380	_	ns	$I_C = 4A$, $I_B = 40mA$, $V_{CC} = 10V$

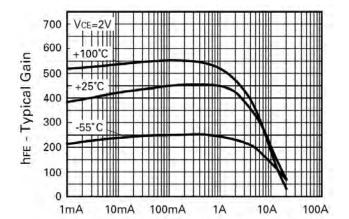
Notes: 9. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%



Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

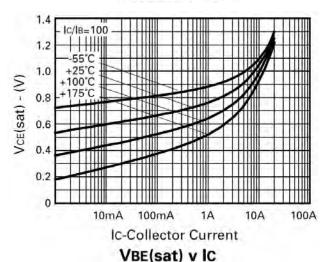


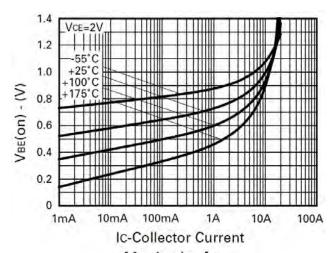




Ic-Collector Current

hFE V IC

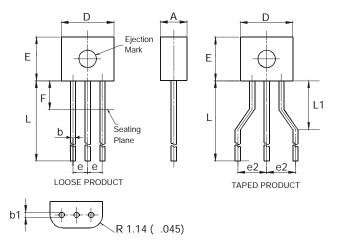






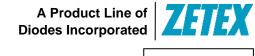
Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



E-Line					
Dim	Min	Max	Тур		
Α	2.16	2.41	-		
b	0.41	0.495	_		
b1	0.41	0.495	-		
D	4.37	4.77	-		
Е	3.61	4.01	-		
е	_	_	1.27		
e2	_	_	2.54		
F	_	2.50	-		
L	13.00	13.97	_		
L1	2.50	3.50	-		
All	All Dimensions in mm				





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